IN THE SPECIFICATION:

Paragraph spanning pages 4 and 5, please delete and replace with the following new paragraph:

Fig. 8 is a diagrammatic sectional view of the nitride-based semiconductor laser fabricated in accordance with a ~~further prior art~~ fabricating method ~~(~~disclosed in Japanese Patent Application ~~Pre-examination Publication~~ No. ~~JP-A-08-343125)~~Heisei 08-343125 which was laid open on July 21, 1998 as JP-A-190142. Now, the structure of the prior ~~art~~ nitride-based semiconductor laser ~~includes~~ shown in Fig. 8 will be described. On a sapphire substrate 201 having a principal surface of a (110) plane, there are formed a 300 Å-thick undoped gallium nitride buffer layer 102 grown at a low temperature, a 3 μm-thick contact layer 103 of silicon-doped n-type gallium nitride, a 0.1 μm-thick crack preventing layer 104 of silicon-doped n-type In0.05Ga0.95N, a 0.4 μm-thick clad layer 105 of silicon-doped n-type Al0.07Ga0.93N, a 0.1 μm-thick light guide layer 106 of silicon-doped n-type gallium nitride, a multi-quantum well structure active layer 107 of seven periods consisting of 25 Å-thick undoped In0.2Ga0.8N quantum well layers and 50 Å-thick undoped In0.05Ga0.95N barrier layers, a 200 Å-thick indium dissociation preventing layer 108 of magnesium-doped p-type Al0.2Ga0.8N, a 0.1 μm-thick light guide layer 109 of magnesium-doped p-type gallium nitride, a 0.4 μm-thick clad layer 110 of magnesium-doped p-type Al0.07Ga0.93N, a 0.2 μm-thick layer 214 of magnesium-doped p-type gallium nitride, a 2000Å-thick silicon oxide film 215, a 1.0 μm-thick contact layer 111 of magnesium-doped p-type gallium nitride, a p-electrode 112 formed of nickel (a first layer) and gold (a second layer), and an n-electrode 113 formed of titanium (a first layer) and aluminum (a second layer). All of the semiconductor layers of the prior art nitride-based semiconductor laser shown in Fig. 8 are a hexagonal crystal having a surface of a (0001) plane.

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Paragraph spanning pages 5 and 6, please delete and replace with the following new paragraph:

A method for fabricating the prior ~~art~~ nitride-based semiconductor laser shown in Fig. 8 will be described. First, on the planar sapphire substrate 201, the low-temperature-grown gallium nitride buffer layer 102, the n-type gallium nitride contact layer 103, the n-type In0.05Ga0.95N crack preventing layer 104, the n-type Al0.07Ga0.93N clad layer 105, the n-type gallium nitride light guide layer 106, the multi-quantum well structure active layer 107, the p-type Al0.2Ga0.8N indium dissociation preventing layer 108, the p-type gallium nitride light guide layer 109, the p-type Al0.07Ga0.93N clad layer 110 and the p-type gallium nitride layer 214, are formed in the named order. Thereafter, the silicon oxide film 215 having openings in the form of a stripe having a width of 5μm in a [100] orientation of the crystal of the n-type gallium nitride contact layer 103 or the p-type gallium nitride layer 214, is formed by a thermal chemical vapor deposition. Then, by use of a metal organic chemical vapor deposition using ammonia as a V-group material, and by using the thus formed silicon oxide film 215 as a mask, the p-type gallium nitride contact layer 111 is selectively formed in only the opening at a substrate temperature of 1050°C. Fig. 9 is a diagrammatic sectional view when this process has been completed. In the silicon oxide film 215, the stripe-shaped openings having the width of 5μm are formed with intervals of 900μm.

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